

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	test and (parasitic adj inductance) and (lc with oscillator) and varactor and frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:11
S2	0	(test with sturcture) and (parasitic adj inductance) and (lc with oscillator) and varactor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:32
S3	0	(test with structure) and (parasitic adj inductance) and (lc with oscillator) and varactor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:32
S4	17	test and (parasitic adj inductance) and varactor and frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 15:59
S5	9599	257/48,E21.524.ccls. 331/105. ccls. 324/500,537,750,763,765, 555,600,612,649,654,655,656, 657.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:04
S6	3518	(parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:47
S7	52	S5 and S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S8	2	S5 and S6 and varactor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:12
S9	938	(parasitic adj inductance).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:23

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S10	3	S9 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:23
S11	1	(parasitic adj inductance) and substructure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:24
S12	87	(parasitic adj inductance) and varactor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:47
S13	2	S12 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:47
S14	17	(parasitic adj inductance) and varactor and test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S15	17	((measure or measurement) with inductance) and varactor and test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:01
S16	17	S15 not S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:52
S17	2	on-chip adj parasitic adj inductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:06
S18	0	(test adj structure) and (integrated adj circuit) and (semiconductor adj wafer) and (lc adj oscillator) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:09
S19	0	(test) and (integrated adj circuit) and (semiconductor adj wafer) and (lc adj oscillator) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:08

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S20	0	(integrated adj circuit) and (semiconductor adj wafer) and (lc adj oscillator) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:08
S21	0	(semiconductor adj wafer) and (lc adj oscillator) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:09
S22	0	wafer and (lc adj oscillator) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:09
S23	17	test and (parasitic adj inductance) and varactor and frequency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:09
S24	9	(test adj structure) and (integrated adj circuit) and (semiconductor adj wafer) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:09
S25	0	(test adj structure) and (integrated adj circuit) and (semiconductor adj wafer) and (parasitic adj inductance) and lc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:10
S26	3	(integrated adj circuit) and (semiconductor adj wafer) and (parasitic adj inductance) and lc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:31
S27	4	(semiconductor adj wafer) and (parasitic adj inductance) and lc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:20
S28	59	(semiconductor adj wafer) and (parasitic adj inductance) and test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:48
S29	18	(semiconductor adj wafer) and (parasitic adj inductance) and (test adj (structure or circuit))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:01

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S30	59	(semiconductor adj wafer) and (parasitic adj inductance) and test and inductance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 12:48
S31	3	varactor and (semiconductor adj wafer) and (parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:13
S32	36	(parasitic adj inductance) and (integrated adj circuit) and (oscillation same frequency) and test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:25
S33	0	(parasitic adj inductance) and (integrated adj circuit) and (oscillation same frequency) and test and (voltage with sweep)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 15:24
S34	23	(parasitic adj inductance) and (integrated adj circuit) and (oscillation same frequency) and test and (wafer or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:02
S35	7	test and (parasitic adj inductance) and varactor and frequency and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S36	10202	257/48,E21.524.ccls. 331/105. ccls. 324/500,537,750,763,765, 555,600,612,649,654,655,656, 657.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S37	3982	(parasitic adj inductance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S38	4	S36 and S37 and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00
S39	7	(parasitic adj inductance) and varactor and test and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:00

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S40	3	((measure or measurement) with inductance) and varactor and test and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:01
S41	1	(semiconductor adj wafer) and (parasitic adj inductance) and (test adj (structure or circuit)) and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:01
S42	13	(parasitic adj inductance) and (integrated adj circuit) and (oscillation same frequency) and test and (wafer or substrate) and @pd>"20050518"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:02
S43	26	S35 S38 S39 S40 S41 S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:05
S44	0	((test adj structure) and (parasitic adj inductance) and (lc adj oscillator) and substructure and varactor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/24 16:06